In The Specification:

Please amend the paragraph as indicated [0012] at page 4 as follows:

[0012] FIG. 2 is a cross-sectional view of an LDMOS transistor **100**. The LDMOS transistor **100** includes a P-substrate **90**. The LDMOS transistor **100** further includes a first diffusion region **33** and a second diffusion region **37** containing N conductivity-type ions to form an N-well **30** with an ion-doped concentration of 5E15/cm^{-3}~5E16/cm^{-3} in the P-substrate **90**. The first diffusion region **33** further comprises an extended drain region **50** with an ion-doped concentration of 5E15/cm^{-3}~5E16/cm^{-3}. A drain diffusion region **53** having N+ conductivity-type ions concentration of 5E19/cm^{-3}~5E20/cm^{-3} in the N-well **30** formed in the first diffusion region **33**, develops a drain region **52** with a boundary ion-doped concentration of 5E15/cm^{-3}~5E16/cm^{-3} in the extended drain region **50**. A third diffusion region containing P conductivity-type ions forms a P-field **60**, divided P-fields **61** and **62** located in the extended drain region **50**. The divided P-fields **61** and **62** are nearer to the drain region **52** than the P-field **60**. A fourth diffusion region **67** containing P conductivity-type ions in the N-well **30** formed by the second diffusion region **37**, develops an isolated P-well **65** for preventing from breakdown. Furthermore, it is well known in the semiconductor manufacturing field that after thermal diffusion of implanted ions, it can make a left edge of the first diffusion region 33 touch a right edge of the second diffusion region 37, which is the source-gap 72 having an ion-doped concentration of 5E14/cm^{-3}~5E15/cm^{-3}. ~~The isolated P-well 65 encloses the source region 56 and the contact region 58.~~ A source diffusion region **55** having N+ conductivity-type ion[[s]] concentration of 5E19/cm^{-3}~5E20/cm^{-3} develops a source region **56** with a boundary ion-doped concentration of 1E16/cm^{-3}~1E17/cm^{-3} in the P well **65**. A contact diffusion region **57** containing

P+ conductivity-type ions concentration of $5E19/cm^{-3}$~$5E20/cm^{-3}$ in the N-well **30** formed by the second diffusion region **37**, develops a contact region **58**. The P-field **60**, the divided P-fields **61** and **62** form junction-fields in the N-well **30** to deplete a drift region.